

## AMENDMENTS TO THE CLAIMS

1.-6. (Canceled)

7. (Currently Amended) A method comprising:

forming an interlayer dielectric comprising alternating layers of dissimilar dielectric materials in a multilayer stack over a metal layer of a device structure;

forming a via having a corrugated sidewall;

forming a decoupling capacitor stack in the via that conforms to the sidewall of the via after forming the decoupling capacitor stack, forming a passivation layer on the decoupling capacitor stack; and

after forming the passivation layer, forming a conductive material in the via, wherein the passivation layer is disposed between the conductive layer and the decoupling capacitor stack.

8. (Original) The method of claim 7, further comprising:

forming the interlayer dielectric layer by depositing alternating layers of dielectric material of different etch selectivities.

9. (Original) The method of claim 8, further comprising:

forming the via using an etch chemistry having an anisotropic etch characteristic toward one of alternative layers of dielectric material.

10. (Original) The method of claim 7, further comprising:

forming the via by etching the via with a wet HF etch to form the corrugated vertical surfaces.

11. (Original) The method of claim 7, further comprising:

depositing the decoupling capacitor stack in the via that conforms to the vertical corrugations of the via by atomic layer chemical vapor deposition.

12.-16. (Canceled)